Product data sheet

1. General description

High voltage, high speed, planar passivated NPN power switching transistor in a SOT54 (TO-92) plastic package.

2. Features and benefits

- Fast switching
- · High voltage capability
- · Very low switching and conduction losses

3. Applications

- Compact fluorescent lamps (CFL)
- Electronic lighting ballasts
- Inverters
- · Off-line self-oscillating power supplies

4. Pinning information

Table 1. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		С
2	С	collector		В
3	Е	emitter		
				E sym123
			TO-92 (SOT54)	·

5. Ordering information

Table 2. Ordering information

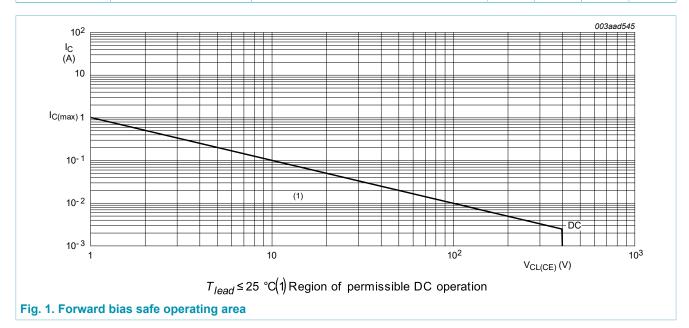
Type number	Package						
	Name	Description	Version				
BUJ100LR	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54				

6. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V	-	700	V
V_{CBO}	collector-base voltage	I _E = 0 A	-	700	V
V_{CEO}	collector-emitter voltage	I _B = 0 A	-	400	V
V_{EBO}	emitter-base voltage	I _C = 0 A; I(Emitter) = 10 mA	-	9	V
I _C	collector current	DC; Fig. 1	-	1	Α
I _{CM}	peak collector current		-	2	Α
I _B	base current	DC	-	0.5	Α
I _{BM}	peak base current		-	1	Α
P _{tot}	total power dissipation	T _{lead} ≤ 25 °C; <u>Fig. 2</u>	-	2.1	W
T _{stg}	storage temperature		-65	150	°C
Tj	junction temperature		-	150	°C



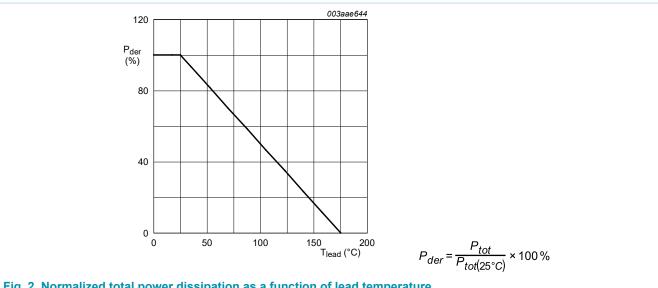


Fig. 2. Normalized total power dissipation as a function of lead temperature

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7. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-lead)}	thermal resistance from junction to lead	<u>Fig. 3</u>	-	-	60	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	printed circuit board mounted; lead length 4 mm	-	150	-	K/W

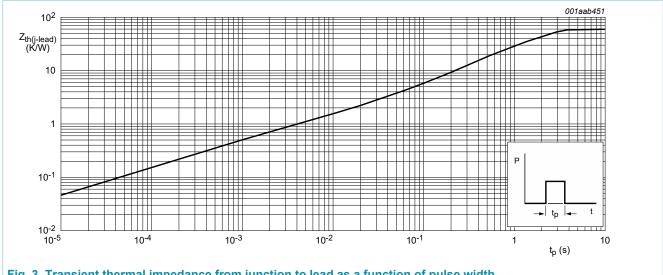


Fig. 3. Transient thermal impedance from junction to lead as a function of pulse width

8. Characteristics

Table 5. Characteristics

Symbol	Parameter	Conditions	l l	Viin	Тур	Max	Unit
Static chara	acteristics						
I _{CES}	collector-emitter cut-off current (base shorted)	$V_{BE} = 0 \text{ V}; V_{CE} = 700 \text{ V}; T_j = 125 \text{ °C}$	-	,	-	5	mA
I _{EBO}	emitter-base cut-off current (collector open)	$V_{EB} = 9 \text{ V}; I_{C} = 0 \text{ A}; T_{lead} = 25 \text{ °C}$	-		-	1	mA
V_{CEOsus}	collector-emitter sustaining voltage (base open)	$I_B = 0 \text{ A}; I_C = 1 \text{ mA}; L_C = 25 \text{ mH};$ $T_{lead} = 25 \text{ °C}; \underline{Fig. 4}; \underline{Fig. 5}$	2	100	-	-	V
V _{CEsat}	collector-emitter saturation voltage	$I_C = 0.25 \text{ A}$; $I_B = 50 \text{ mA}$; $T_{lead} = 25 ^{\circ}\text{C}$; Fig. 6	-	,	0.2	0.5	V
		I_C = 0.5 A; I_B = 125 mA; T_{lead} = 25 °C; Fig. 6	-		0.3	1	V
		$I_C = 0.75 \text{ A}$; $I_B = 250 \text{ mA}$; $T_{lead} = 25 ^{\circ}\text{C}$; Fig. 6	-		0.4	1.5	V
V _{BEsat}	base-emitter saturation voltage	$I_C = 0.25 \text{ A}$; $I_B = 50 \text{ mA}$; $T_{lead} = 25 ^{\circ}\text{C}$; Fig. 7	-		-	1	V
		$I_C = 0.5 \text{ A}$; $I_B = 125 \text{ mA}$; $T_{lead} = 25 ^{\circ}\text{C}$; Fig. 7	-		-	1.2	V
h _{FE}	DC current gain	I_C = 0.5 mA; V_{CE} = 2 V; T_{lead} = 25 °C	1	12	-	-	
		I _C = 0.4 A; V _{CE} = 5 V; T _{lead} = 25 °C; <u>Fig. 8; Fig. 9</u>	1	10	-	30	
		I _C = 0.8 A; V _{CE} = 5 V; T _{lead} = 25 °C; <u>Fig. 8; Fig. 9</u>	5	5	7.5	20	
Dynamic ch	naracteristics					1	
t _f	fall time	I_C = 1 A; I_{Bon} = 200 mA; V_{BB} = -5 V; L_B = 1 μ H; T_{lead} = 25 °C; inductive load; Fig. 10; Fig. 11	-		80	-	ns

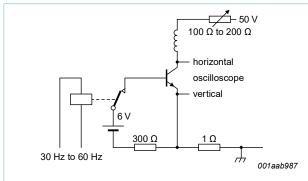


Fig. 4. Test circuit for collector-emitter sustaining voltage

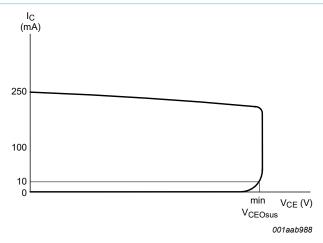


Fig. 5. Oscilloscope display for collector-emitter sustaining voltage test waveform

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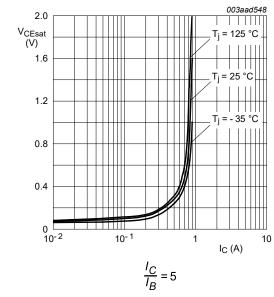


Fig. 6. Collector-emitter saturation voltage as a function of collector current; typical values

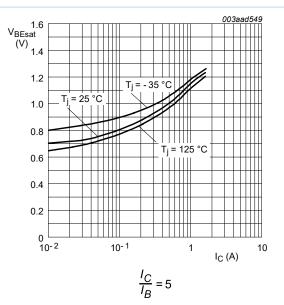


Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

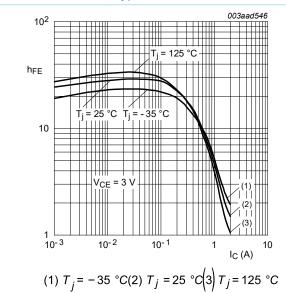


Fig. 8. DC current gain as a function of collector current; typical values

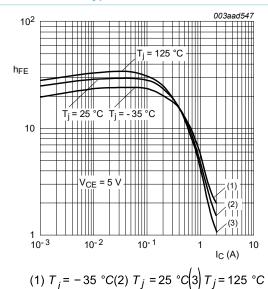
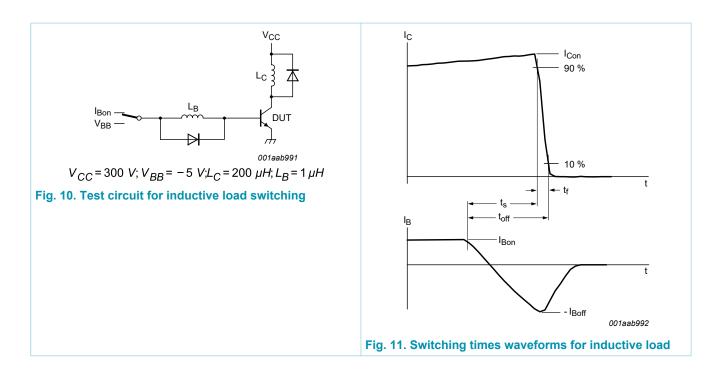


Fig. 9. DC current gain as a function of collector current; typical values

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9. Package outline

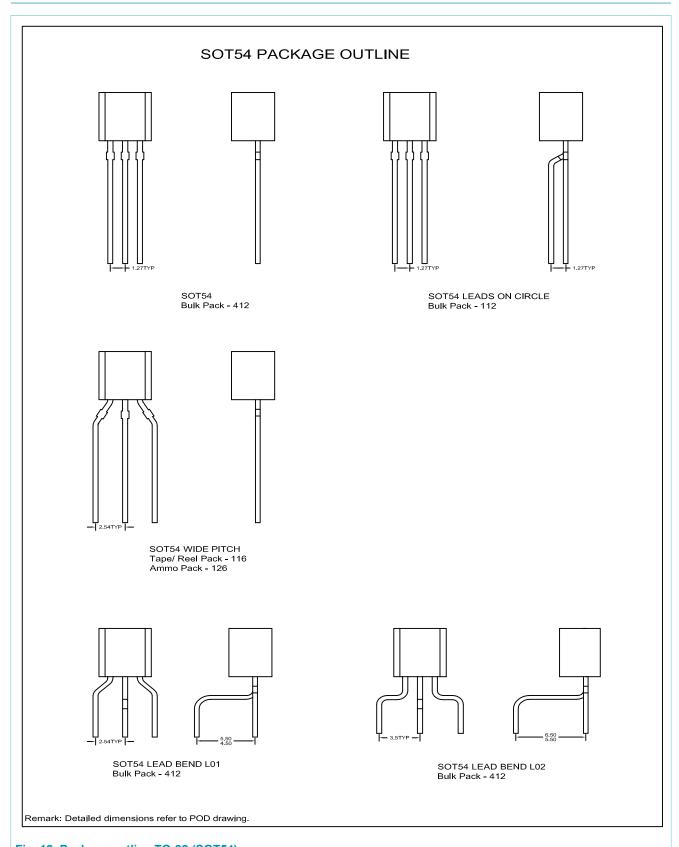


Fig. 12. Package outline TO-92 (SOT54)

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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